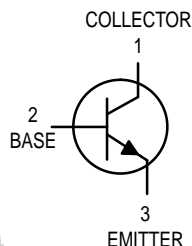


# Low Noise Transistors

## NPN Silicon

**BC549B,C**  
**BC550B,C**

 CASE 29-04, STYLE 17  
 TO-92 (TO-226AA)

### MAXIMUM RATINGS

Rating	Symbol	BC549	BC550	Unit
Collector–Emitter Voltage	$V_{CE0}$	30	45	Vdc
Collector–Base Voltage	$V_{CBO}$	30	50	Vdc
Emitter–Base Voltage	$V_{EBO}$		5.0	Vdc
Collector Current — Continuous	$I_C$	100		mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625	5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5	12	Watt mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	–55 to +150		$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ( $I_C = 10 \text{ mAdc}, I_B = 0$ )	BC549B,C BC550B,C	$V_{(BR)CEO}$	30 45	— —	— —	Vdc
Collector–Base Breakdown Voltage ( $I_C = 10 \text{ }\mu\text{Adc}, I_E = 0$ )	BC549B,C BC550B,C	$V_{(BR)CBO}$	30 50	— —	— —	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 10 \text{ }\mu\text{Adc}, I_C = 0$ )		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ( $V_{CB} = 30 \text{ V}, I_E = 0$ ) ( $V_{CB} = 30 \text{ V}, I_E = 0, T_A = +125^\circ\text{C}$ )		$I_{CBO}$	— —	— —	15 5.0	nAdc $\mu\text{Adc}$
Emitter Cutoff Current ( $V_{EB} = 4.0 \text{ Vdc}, I_C = 0$ )		$I_{EBO}$	—	—	15	nAdc

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>ON CHARACTERISTICS</b>					
DC Current Gain ( $I_C = 10\ \mu\text{Adc}$ , $V_{CE} = 5.0\ \text{Vdc}$ )	$h_{FE}$	100	150	—	—
BC549B/550B		100	270	—	—
( $I_C = 2.0\ \text{mAdc}$ , $V_{CE} = 5.0\ \text{Vdc}$ )		200	290	450	—
BC549B/550B		420	500	800	—
Collector–Emitter Saturation Voltage ( $I_C = 10\ \text{mAdc}$ , $I_B = 0.5\ \text{mAdc}$ )	$V_{CE(sat)}$	—	0.075	0.25	Vdc
( $I_C = 10\ \text{mAdc}$ , $I_B = \text{see note 1}$ )		—	0.3	0.6	
( $I_C = 100\ \text{mAdc}$ , $I_B = 5.0\ \text{mAdc}$ , see note 2)		—	0.25	0.6	
Base–Emitter Saturation Voltage ( $I_C = 100\ \text{mAdc}$ , $I_B = 5.0\ \text{mAdc}$ )	$V_{BE(sat)}$	—	1.1	—	Vdc
Base–Emitter On Voltage ( $I_C = 10\ \mu\text{Adc}$ , $V_{CE} = 5.0\ \text{Vdc}$ )	$V_{BE(on)}$	—	0.52	—	Vdc
( $I_C = 100\ \mu\text{Adc}$ , $V_{CE} = 5.0\ \text{Vdc}$ )		—	0.55	—	
( $I_C = 2.0\ \text{mAdc}$ , $V_{CE} = 5.0\ \text{Vdc}$ )		0.55	0.62	0.7	

**SMALL–SIGNAL CHARACTERISTICS**

Current–Gain — Bandwidth Product ( $I_C = 10\ \text{mAdc}$ , $V_{CE} = 5.0\ \text{Vdc}$ , $f = 100\ \text{MHz}$ )	$f_T$	—	250	—	MHz
Collector–Base Capacitance ( $V_{CB} = 10\ \text{Vdc}$ , $I_E = 0$ , $f = 1.0\ \text{MHz}$ )	$C_{cbo}$	—	2.5	—	pF
Small–Signal Current Gain ( $I_C = 2.0\ \text{mAdc}$ , $V_{CE} = 5.0\ \text{V}$ , $f = 1.0\ \text{kHz}$ )	$h_{fe}$	240	330	500	—
BC549B/BC550B		450	600	900	—
Noise Figure ( $I_C = 200\ \mu\text{Adc}$ , $V_{CE} = 5.0\ \text{Vdc}$ , $R_S = 2.0\ \text{k}\Omega$ , $f = 1.0\ \text{kHz}$ )	$NF_1$	—	0.6	2.5	dB
	$NF_2$	—	—	10	
( $I_C = 200\ \mu\text{Adc}$ , $V_{CE} = 5.0\ \text{Vdc}$ , $R_S = 100\ \text{k}\Omega$ , $f = 1.0\ \text{kHz}$ )					

NOTES:

- $I_B$  is value for which  $I_C = 11\ \text{mA}$  at  $V_{CE} = 1.0\ \text{V}$ .
- Pulse test =  $300\ \mu\text{s}$  – Duty cycle = 2%.

*Electrónica S.A. de C.V.*

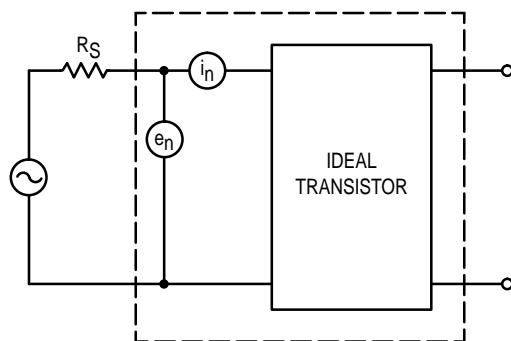


Figure 1. Transistor Noise Model

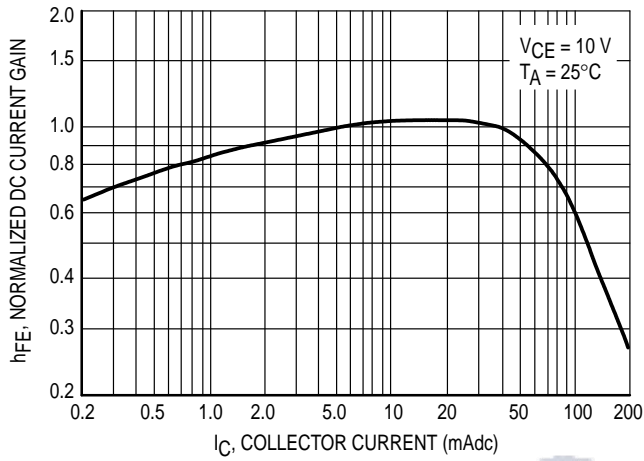


Figure 2. Normalized DC Current Gain

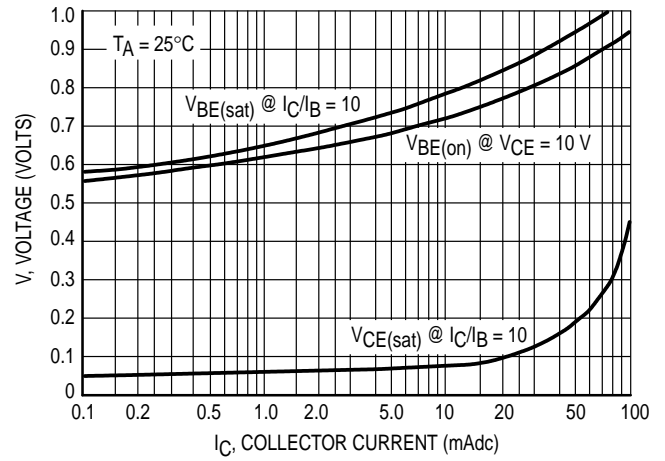


Figure 3. "Saturation" and "On" Voltages

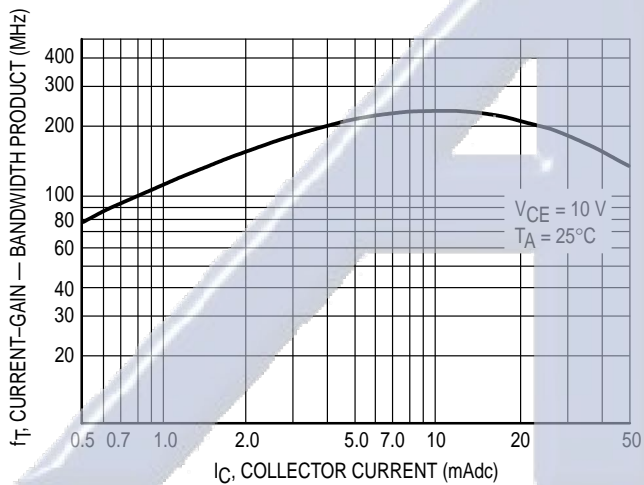


Figure 4. Current-Gain — Bandwidth Product

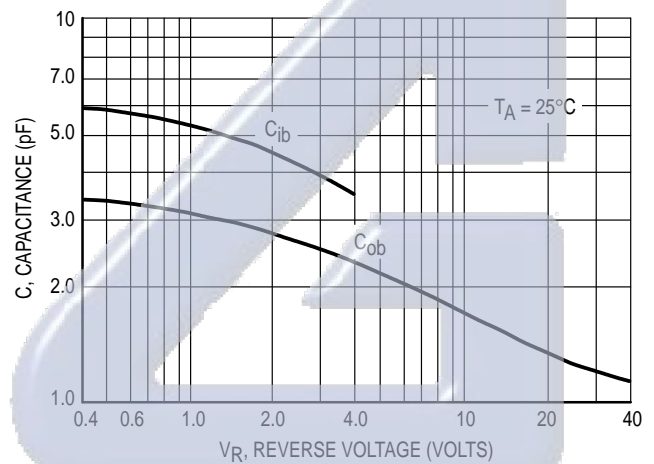


Figure 5. Capacitance

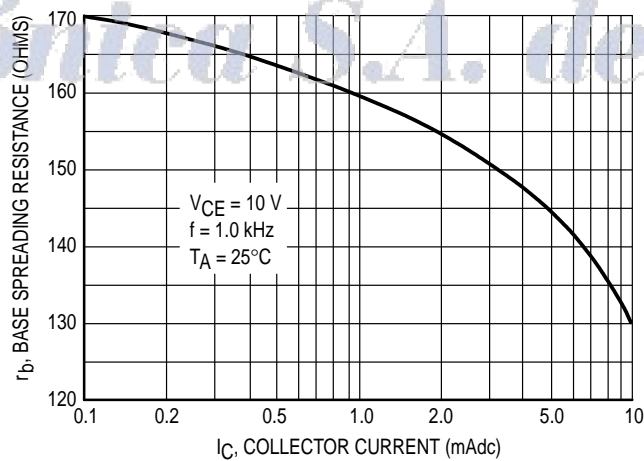
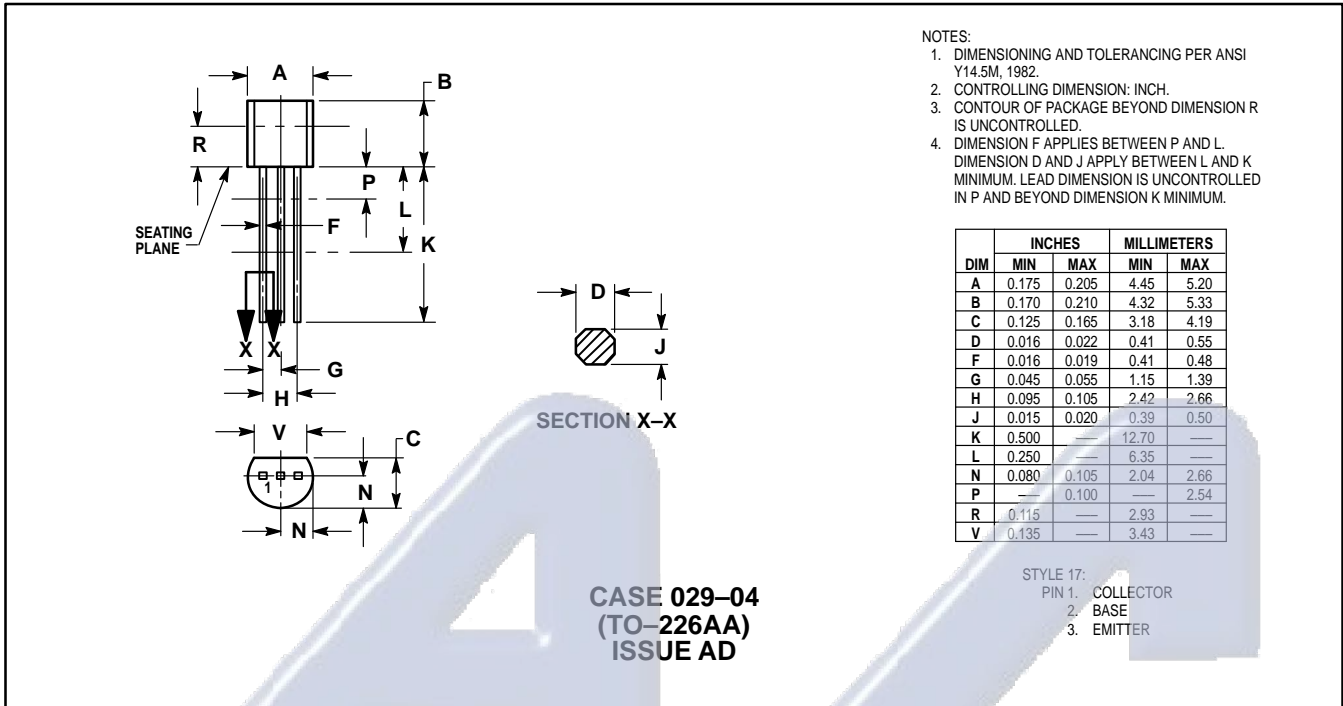


Figure 6. Base Spreading Resistance

PACKAGE DIMENSIONS



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